

# **Amplifier Transistor**

### **NPN Silicon**

## **MMBT8099LT1G**

#### **Features**

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	80	Vdc
Collector-Base Voltage	$V_{CBO}$	80	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	500	mAdc

#### THERMAL CHARACTERISTICS

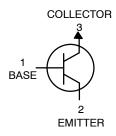
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062 \text{ in.}$
- 2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.



SOT-23 (TO-236) CASE 318 STYLE 6



#### **MARKING DIAGRAM**



KB = Specific Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may
vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBT8099LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### MMBT8099LT1G

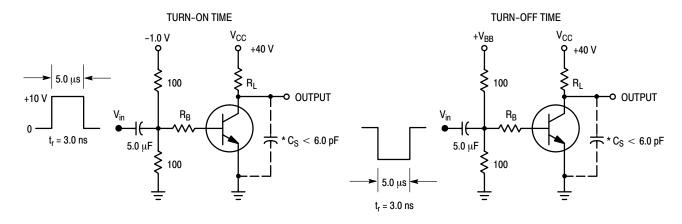
## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	
Collector – Emitter Breakdown Voltage (Note 3) $(I_C = 10 \text{ mAdc}, I_B = 0)$	V <sub>(BR)</sub> CEO	80	_	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	V <sub>(BR)</sub> CBO	80	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	6.0	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, I <sub>B</sub> = 0)	Ices	-	0.1	μAdc
Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_{E} = 0)$ $(V_{CB} = 80 \text{ Vdc}, I_{E} = 0)$	I <sub>CBO</sub>	- -	0.1 -	μAdc
Emitter Cutoff Current ( $V_{EB} = 6.0 \text{ Vdc}, I_{C} = 0$ ) ( $V_{EB} = 4.0 \text{ Vdc}, I_{C} = 0$ )	I <sub>EBO</sub>	<u>-</u>	0.1 -	μAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain	h <sub>FE</sub>	100 100 75	300 - -	-
Collector – Emitter Saturation Voltage ( $I_C = 100 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ ) ( $I_C = 100 \text{ mAdc}$ , $I_B = 10 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	_ _	0.4 0.3	Vdc
$\begin{aligned} & \text{Base-Emitter On Voltage} \\ & \text{(I}_{\text{C}} = 1.0 \text{ mAdc, V}_{\text{CE}} = 5.0 \text{ Vdc)} \\ & \text{(I}_{\text{C}} = 10 \text{ mAdc, V}_{\text{CE}} = 5.0 \text{ Vdc)} \end{aligned}$	V <sub>BE(on)</sub>	_ 0.6	_ 0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	fτ	150	_	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	6.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	-	25	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

#### MMBT8099LT1G



\*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

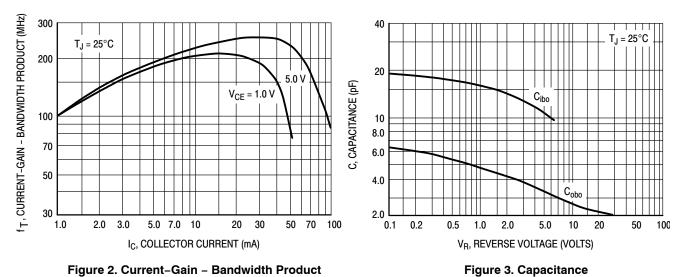


Figure 2. Current-Gain - Bandwidth Product

1.0 k

700

500

300

200

70

50

30

20

10

t, TIME (ns) 100 V<sub>CC</sub> = 40 V

 $I_C/I_B = 10$ 

 $T_J = 25^{\circ}C$ 

 $t_d @ V_{BE(off)}$ 

= 0.5 V

20

 $I_{B1} = I_{B2}$ 

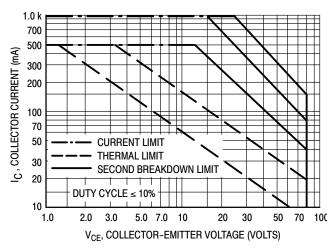


Figure 4. Switching Times

IC, COLLECTOR CURRENT (mA)

100



#### MMBT8099LT1G

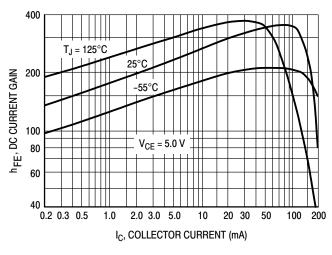


Figure 6. DC Current Gain

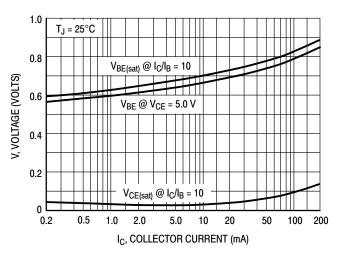


Figure 7. "ON" Voltages

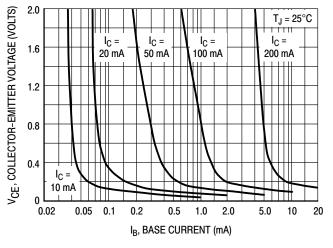


Figure 8. Collector Saturation Region

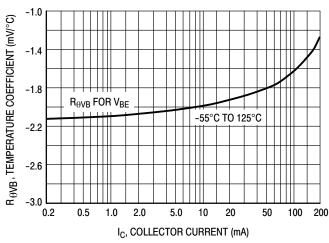


Figure 9. Base-Emitter Temperature Coefficient

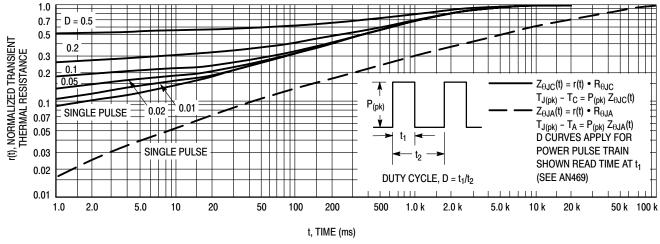


Figure 10. Thermal Response

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

\_\_\_





#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

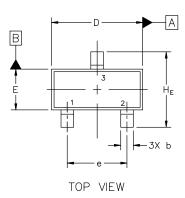
2.04

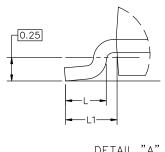
0.55

0.69

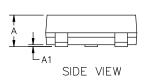
2.64

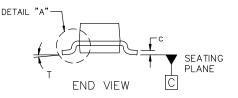
10°

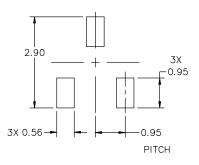




DETAIL "A" Scale 3:1







#### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

#### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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